

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

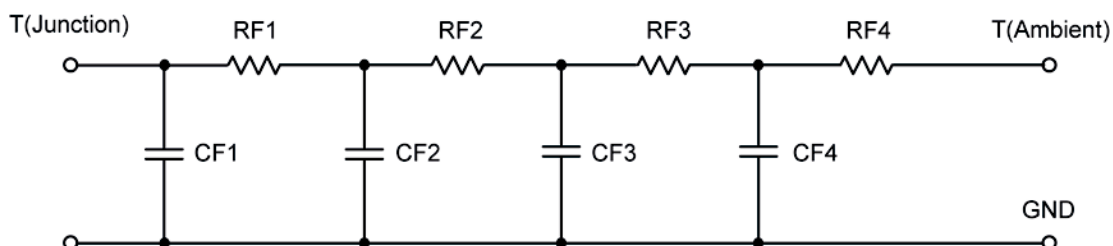
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	31.3037	N/A	1.5595
RT2	7.2452	N/A	13.3375
RT3	14.8649	N/A	2.8692
RT4	41.5862	N/A	2.2338
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	7.0168 m	N/A	5.2279 m
CT2	605.3506 u	N/A	2.3994 m
CT3	608.6586 m	N/A	707.1591 u
CT4	1.9167	N/A	402.0757 u

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	7.2525	N/A	5.4794
RF2	31.3666	N/A	10.8326
RF3	18.1152	N/A	1.3472
RF4	38.2657	N/A	2.3408
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	434.0024 u	N/A	217.9399 u
CF2	5.8795 m	N/A	1.2158 m
CF3	349.3162 m	N/A	7.2726 m
CF4	1.4747	N/A	14.2732 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

